# SK 25 WT



# SEMITOP<sup>®</sup> 2

### Antiparallel Thyristor Module

#### SK 25 WT

Preliminary Data

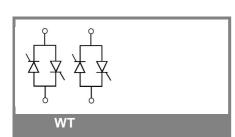
#### Features

- Compact Design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DBC)
- Glass passived thyristor chips
- Up to 1600V reverse voltage
- UL recognized, file no. E 63 532

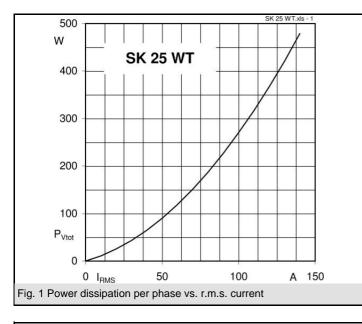
### **Typical Applications**

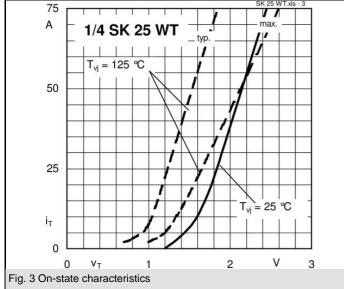
- Soft starters
- Light control (studios, theaters...)
- Temperature control

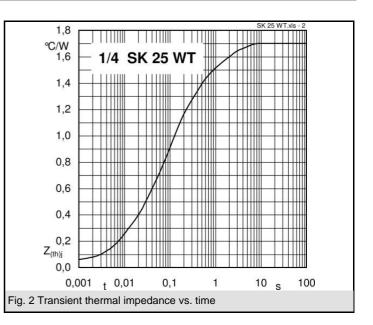
V <sub>RSM</sub>	V <sub>RRM</sub> , V <sub>DRM</sub>	I <sub>RMS</sub> = 29 A A (full conduction	)	
V	V	(T <sub>s</sub> = 85 °C)	ŕ	
900	800	SK 25 WT 08		
1300 1200			SK 25 WT 12	
1700 1600		SK 25 WT 16		
1700	1000	SK 25 W1 10		
Symbol	Conditions	Values	Units	
I <sub>RMS</sub>	W1C ; sin. 180° ; T <sub>s</sub> = 100	20	А	
	W1C ; sin. 180° ; T <sub>s</sub> = 85°	29	А	
I <sub>TSM</sub>	T <sub>vi</sub> = 25 °C ; 10 ms	320	А	
	T <sub>vi</sub> = 125 °C ; 10 ms	280	А	
i²t	T <sub>vi</sub> = 25 °C ; 8,310 ms	510	A²s	
	T <sub>vj</sub> = 125 °C ; 8,310 ms	390	A²s	
V <sub>T</sub>	T <sub>vi</sub> = 25 °C, I <sub>T</sub> = 75 A	max. 2,45	V	
V <sub>T(TO)</sub>	T <sub>vi</sub> = 125 °C	max. 1,1	V	
r <sub>T</sub>	T <sub>vi</sub> = 125 °C	max. 20	mΩ	
I <sub>DD</sub> ;I <sub>RD</sub>	T <sub>vj</sub> = 125 °C, V <sub>RD</sub> =V <sub>RRM</sub>	max. 8	mA	
t <sub>gd</sub>	$T_{vj} = 125 \text{ °C}, V_{RD} = V_{RRM}$ $T_{vj} = 25 \text{ °C}, I_G = 1 \text{ A}; di_G/d$	• 1 Α/μs 1	μs	
t <sub>gr</sub>	V <sub>D</sub> = 0,67 *V <sub>DRM</sub>	1	μs	
(dv/dt) <sub>cr</sub>	T <sub>vi</sub> = 125 °C	1000	V/µs	
(di/dt) <sub>cr</sub>	T <sub>vi</sub> = 125 °C; f= 5060 Hz	50	A/μs	
t <sub>q</sub>	T <sub>vi</sub> = 125 °C; typ.	80	μs	
I <sub>H</sub>	T <sub>vi</sub> = 25 °C; typ. / max.	80 / 150	mA	
IL	$T_{vj} = 25$ °C; $R_{G} = 33 \Omega$ ; ty	/ max. 150 / 300	mA	
V <sub>GT</sub>	T <sub>vi</sub> = 25 °C; d.c.	min. 2	V	
I <sub>GT</sub>	T <sub>vi</sub> = 25 °C; d.c.	min. 100	mA	
V <sub>GD</sub>	T <sub>vi</sub> = 125 °C; d.c.	max. 0,25	V	
I <sub>GD</sub>	T <sub>vj</sub> = 125 °C; d.c.	max. 3	mA	
R <sub>th(j-s)</sub>	cont. per thyristor	1,7	K/W	
	sin 180° per thyristor	1,78	K/W	
R <sub>th(j-s)</sub>	cont. per W1C	0,85	K/W	
	sin 180° per W1C	0,89	K/W	
T <sub>vj</sub>		-40 +125	°C	
T <sub>stg</sub>		-40 +125	°C	
T <sub>solder</sub>	terminals, 10s	260	°C	
V <sub>isol</sub>	a. c. 50 Hz; r.m.s.; 1 s / 1	in. 3000 / 2500	V~	
M <sub>s</sub>	Mounting torque to heatsir	2,5	Nm	
M <sub>t</sub>			Nm	
а			m/s²	
m		19	g	
Case	SEMITOP <sup>®</sup> 2	Т 37		

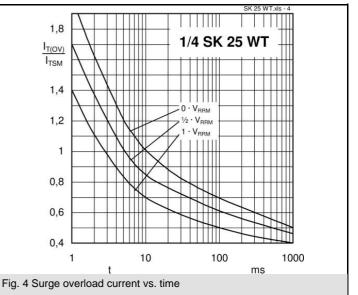


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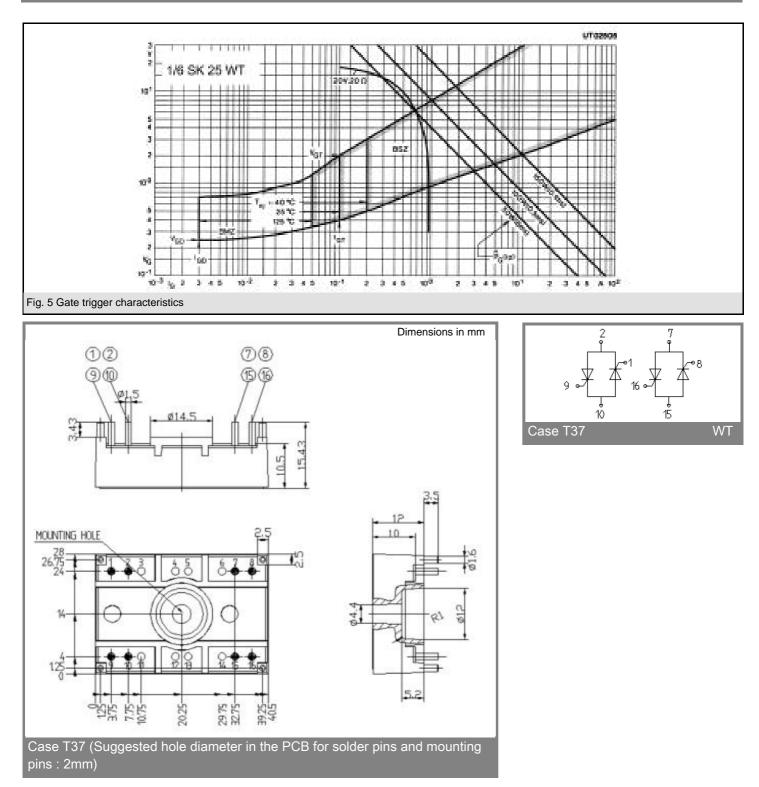








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